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	AA						
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<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes    No
	AM						
<b>OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)</b>							
yfg	AN		ARMAS, B., et al., "Chemical Vapor Deposition Of Si <sub>3</sub> N <sub>4</sub> and AlN on Carbon Fibers", <u>Chemical Vapor Deposition 1987</u> , The Electrochemical Society, Inc., Proceedings Vol 87-8, pp. 1060-69 (1987)				
	AO		SUZUKI, M., et al., "CVD Of Polycrystalline Aluminum Nitride", <u>Chemical Vapor Deposition 1987</u> , The Electrochemical Society, Inc., Proceedings Vol 87-8, pp. 1089-97 (1987)				
	AP		KOBAYASHI, N., et al., <u>Improved 2DEG Mobility In Selectively Doped GaAs/N-AlGaAs Grown by MOCVD Using Triethyl Organometallic Compounds</u> , Musashino Elect. Comm. Lab., Nippon Tel & Telegraph, Japan, 2 Pages, (9/10/1984)				
	AQ		PIERSON, Hugh O., <u>Handbook Of Chemical Vapor Deposition (CVD)</u> , Noyes Publications, N.J., pp. 216-219 (undated)				
	AR		<u>CVD Of Nonmetals</u> , Editor: William S. Rees, Jr., pp. 301-307 (1996)				
	AS		C. Jimenez et al., <u>Preparation of aluminum nitride films by low pressure organometallic chemical vapor deposition</u> , 76-77 SURFACE AND COATINGS TECHNOLOGY 372-376 (1995).				
yfg	AT		H. Liu et al., <u>The surface chemistry of aluminum nitride MOCVD on alumina using trimethylaluminum and ammonia as precursors</u> , 320 SURFACE SCIENCE 145-160 (1994).				
	EXAMINER		DATE CONSIDERED				
yfg		9/24/02					
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Sheet 1 of 2

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## U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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	AB	5,709,928	01/98	IKEDA ET AL.			
	AC	5,605,858	02/97	NISHIOKA ET AL.			
	AD	5,687,112	11/97	OVSHINSKY			
	AE	5,767,578	06/98	CHANG ET AL.			
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	AI	5,786,635	07/98	ALCOE ET AL.			
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## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
yzh	AS	JP401230779A	09/14/89	Hayashi et al.				

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